

	Hits	Search Text	DBs
51	0	216/66.ccls. and (((resist or photoresist or photosensitive or (radiation near5 sensitive)) near16 (mask or pattern\$4 or opening) near24 (strip\$4 or etch\$4 or (dry near5 etch\$4) or RIE or ash\$4 or mill\$4 or (ion near9 beam near4 etch\$4) or plasma)) same (shrink\$4 or reduc\$4 or remov\$4 or etch\$4 or strip\$4) same (sidewall or surface or profile or pattern or mask or residu\$3) same (((sulfur near2 oxide) or (sul\$3ur near2 \$2oxide) or ("SO.sub.2") or (sul\$2ur near9 containing)) near28 (Ne or Ar or Xe or Kr or "N.sub.2" or nitrogen or neon or argon or xenon or krypton or "CO" or "CO.sub.2" or (carbon near9 dioxide) or (carbon near9 \$4oxide)))) and (BARC or (bottom near5 ARC) or antireflect\$4 or (bottom near4 antireflect\$4 near6 layer)) and (((underlying near4 surface) or line or circuit or via or conductive or substrate) same (layer or film or coating) same (expos\$4 or opening or area or region) same (reduc\$4 or shrink\$4))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
52	4	<p>430/325.ccls. and (((resist or photoresist or photosensitive or (radiation near5 sensitive)) near16 (mask or pattern\$4 or opening) near24 (strip\$4 or etch\$4 or (dry near5 etch\$4) or RIE or ash\$4 or mill\$4 or (ion near9 beam near4 etch\$4) or plasma)) same (shrink\$4 or reduc\$4 or remov\$4 or etch\$4 or strip\$4) same (sidewall or surface or profile or pattern or mask or residu\$3) same (((sulfur near2 oxide) or (sul\$3ur near2 \$2oxide) or ("SO.sub.2") or (sul\$2ur near9 containing)) near28 (Ne or Ar or Xe or Kr or "N.sub.2" or nitrogen or neon or argon or xenon or krypton or "CO" or "CO.sub.2" or (carbon near9 dioxide) or (carbon near9 \$4oxide)))) and (BARC or (bottom near5 ARC) or antireflect\$4 or (bottom near4 antireflect\$4 near6 layer)) and (((underlying near4 surface) or line or circuit or via) same (expos\$4 or opening or area or region) same (reduc\$4 or shrink\$4))</p>	<p>US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB</p>

	Hits	Search Text	DBs
53	1	<p>430/322.ccls. and (((resist or photoresist or photosensitive or (radiation near5 sensitive)) near16 (mask or pattern\$4 or opening) near24 (strip\$4 or etch\$4 or (dry near5 etch\$4) or RIE or ash\$4 or mill\$4 or (ion near9 beam near4 etch\$4) or plasma)) same (shrink\$4 or reduc\$4 or remov\$4 or etch\$4 or strip\$4) same (sidewall or surface or profile or pattern or mask or residu\$3) same (((sulfur near2 oxide) or (sul\$3ur near2 \$2oxide) or ("SO.sub.2") or (sul\$2ur near9 containing)) near28 (Ne or Ar or Xe or Kr or "N.sub.2" or nitrogen or neon or argon or xenon or krypton or "CO" or "CO.sub.2" or (carbon near9 dioxide) or (carbon near9 \$4oxide)))) and (BARC or (bottom near5 ARC) or antireflect\$4 or (bottom near4 antireflect\$4 near6 layer)) and (((underlying near4 surface) or line or circuit or via) same (expos\$4 or opening or area or region) same (reduc\$4 or shrink\$4))</p>	<p>US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB</p>

	Hits	Search Text	DBs
54	6	<p>430/323.ccls. and (((resist or photoresist or photosensitive or (radiation near5 sensitive)) near16 (mask or pattern\$4 or opening) near24 (strip\$4 or etch\$4 or (dry near5 etch\$4) or RIE or ash\$4 or mill\$4 or (ion near9 beam near4 etch\$4) or plasma)) same (shrink\$4 or reduc\$4 or remov\$4 or etch\$4 or strip\$4) same (sidewall or surface or profile or pattern or mask or residu\$3) same (((sulfur near2 oxide) or (sul\$3ur near2 \$2oxide) or ("SO.sub.2") or (sul\$2ur near9 containing)) near28 (Ne or Ar or Xe or Kr or "N.sub.2" or nitrogen or neon or argon or xenon or krypton or "CO" or "CO.sub.2" or (carbon near9 dioxide) or (carbon near9 \$4oxide)))) and (BARC or (bottom near5 ARC) or antireflect\$4 or (bottom near4 antireflect\$4 near6 layer)) and (((underlying near4 surface) or line or circuit or via) same (expos\$4 or opening or area or region) same (reduc\$4 or shrink\$4))</p>	<p>US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB</p>

	Hits	Search Text	DBs
55	26	(((resist or photoresist or photosensitive or (radiation near5 sensitive)) near16 (mask or pattern\$4 or opening) near24 (strip\$4 or etch\$4 or (dry near5 etch\$4) or RIE or ash\$4 or mill\$4 or (ion near9 beam near4 etch\$4) or plasma)) same (shrink\$4 or reduc\$4 or remov\$4 or etch\$4 or strip\$4) same (sidewall or surface or profile or pattern or mask or residu\$3) same (((sulfur near2 oxide) or (sul\$3ur near2 \$2oxide) or ("SO.sub.2") or (sul\$2ur near9 containing)) near28 (Ne or Ar or Xe or Kr or "N.sub.2" or nitrogen or neon or argon or xenon or krypton or "CO" or "CO.sub.2" or (carbon near9 dioxide) or (carbon near9 \$4oxide)))) and (BARC or (bottom near5 ARC) or antireflect\$4 or (bottom near4 antireflect\$4 near6 layer)) and (((underlying near4 surface) or line or circuit or via or conductive or substrate) same (layer or film or coating) same (expos\$4 or opening or area or region) same (reduc\$4 or shrink\$4))	US-PGPUB